a first conductivity type guide layer (706) of a refractive index n_g, an active quantum well layer (707), a second conductivity type guide layer (709), a second conductivity type clad layer (710), and a second conductivity type contact layer (711) deposited in this order, wherein:

said optical waveguide has an effective refractive index $n_e < n_s, n_g$, said first conductivity type clad layer (703; 705) includes a first region, a second region, and a third region in this order in its thickness direction, said second region having an Al composition ratio larger than said first and third regions, and then said first, second and third regions all having their respective refractive indexes smaller than n_e.

13. The nitride semiconductor laser device of claim 12, wherein a total thickness d_t including said first, second and third regions is in a range of $1.4\ \mu m \leq d_t \leq 3.5\ \mu m$.

14. The nitride semiconductor laser device of claim 13, wherein in said second region, a maximum Al composition ratio x_{max} is in a range of $0.06 \leq x_{max} \leq 0.35$.

15. The nitride semiconductor laser device of claim 13, wherein a portion having the maximum Al composition ratio x_{max} in said second region in said first conductivity type clad layer (703; 705) is located at a position farther than $2d_t/3$ in a direction from said substrate toward said active layer.

16. The semiconductor laser device of claim 12, wherein on a laser beam emitting end surface, one of an optical absorber film and an optical reflective film (800) is formed on an optical radiation region (810; 820) below said first conductivity type clad layer (703; 705).

17. The semiconductor laser device of claim 16, wherein said optical absorber